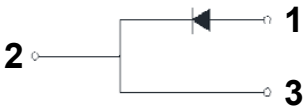
HSTPSC10H12D

Silicon Carbide Schottky Diode

Features

- 1.2kV Schottky Rectifier
- Zero Reverse Recovery Current
- High-Frequency Operation
- Temperature-Independent Switching
- Extremely Fast Switching
- Positive Temperature Coefficient on V_F

TO-220C-2L



Benefits

- Replace Bipolar with Unipolar Rectifiers
- Essentially No Switching Losses
- Higher Efficiency
- Reduction of Heat Sink Requirements
- Parallel Devices Without Thermal Runaway

Applications

- Switch Mode Power Supplies (SMPS)
- Boost diodes in PFC or DC/DC stages
- Free Wheeling Diodes in Inverter stages
- AC/DC converters

Part Number	Package	Qty(PCS)
HSTPSC10H12D	TO-220C-2L	50

Maximum Ratings (T_C=25°C unless otherwise specified)

Symbol	Parameter	Value	Unit	Test Conditions	Note
V_{RRM}	Repetitive Peak Reverse Voltage	1200	V		
V_{RSM}	Surge Peak Reverse Voltage	1300	V		
V_R	DC Peak Reverse Voltage	1200	V		
I_F	Continuous Forward Current	33 16 10	A	T_C=25˚C T_C=135˚C T_C=156˚C	Fig. 3
I_{FRM}	Repetitive Peak Forward Surge Current	47 31.5	A	T_C=25˚C, t_P=10 ms, Half Sine Pulse T_C=110˚C, t_P=10 ms, Half Sine Pulse	
I_{FSM}	Non-Repetitive Forward Surge Current	71 59.5	A	T_C=25˚C, t_P=10 ms, Half Sine Pulse T_C=110˚C, t_P=10 ms, Half Sine Pulse	Fig. 8
$I_{F,Max}$	Non-Repetitive Peak Forward Current	750 620	A	T_C=25˚C, t_P=10 ms, Pulse T_C=110˚C, t_P=10 ms, Pulse	Fig. 8
P_{tot}	Power Dissipation	166.5 72	W	T_C=25˚C T_C=110˚C	Fig. 4
dV/dt	Diode dV/dt ruggedness	200	V/ns	V_R=0-960V	
$\int i^2dt$	i^2t value	25 17.5	A^2s	T_C=25˚C, t_P=10 ms T_C=110˚C, t_P=10 ms	
T_J	Operating Junction Range	-55 to +175	˚C		
T_{stg}	Storage Temperature Range	-55 to +135	˚C		
	TO-220 Mounting Torque	1 8.8	Nm lbf-in	M3 Screw 6-32 Screw	

Electrical Characteristics

Symbol	Parameter	Typ.	Max.	Unit	Test Conditions	Note
V_F	Forward Voltage	1.5 2.2	1.8 3	V	I_F = 10 A T_J=25°C I_F = 10 A T_J=175°C	Fig. 1
I_R	Reverse Current	30 55	250 350	μA	V_R = 1200 V T_J=25°C V_R = 1200 V T_J=175°C	Fig. 2
Q_C	Total Capacitive Charge	52		nC	V_R = 800 V, I_F = 10A d*i*/d*t* = 200 A/μs T_J = 25°C	Fig. 5
C	Total Capacitance	754 45 38		pF	V_R = 0 V, T_J = 25°C, f = 1 MHz V_R = 400 V, T_J = 25°C, f = 1 MHz V_R = 800 V, T_J = 25°C, f = 1 MHz	Fig. 6
E_C	Capacitance Stored Energy	14.5		μJ	V_R = 800 V	Fig. 7

Note:This is a majority carrier diode, so there is no reverse recovery charge.

Thermal Characteristics

Symbol	Parameter	Typ.	Unit	Note
$R_{\theta JC}$	Thermal Resistance from Junction to Case	0.9	°C/W	Fig. 9

Typical Performance

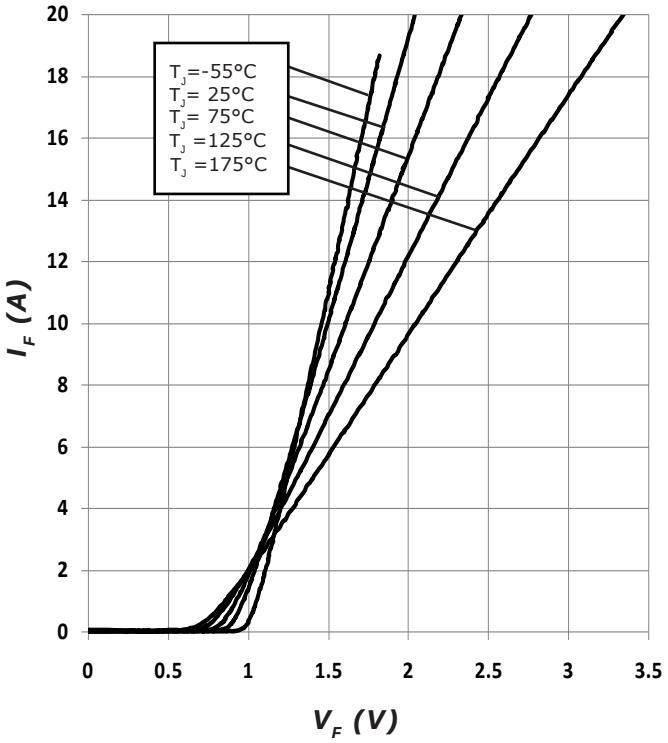


Figure 1. Forward Characteristics

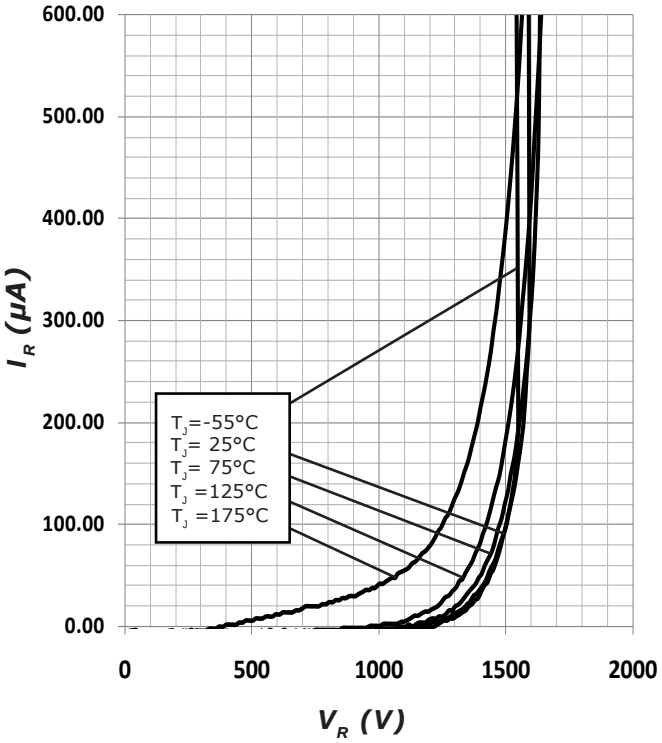


Figure 2. Reverse Characteristics

Typical Performance

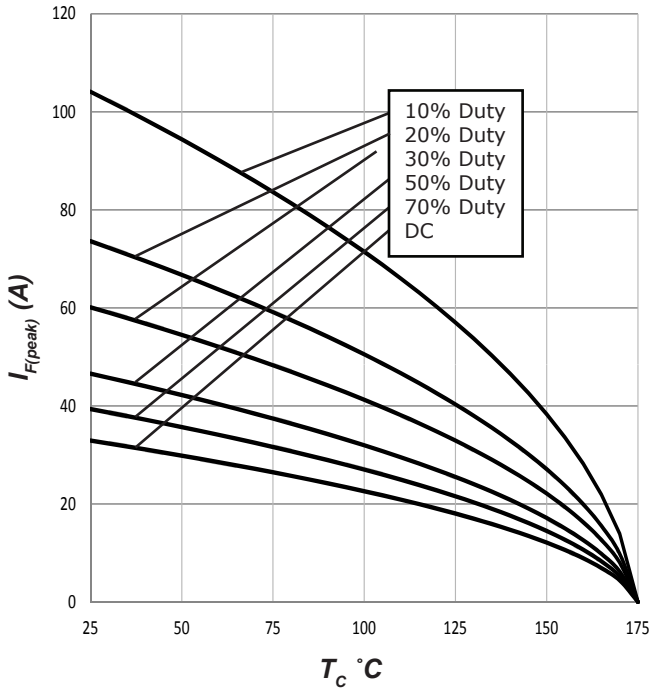


Figure 3. Current Derating

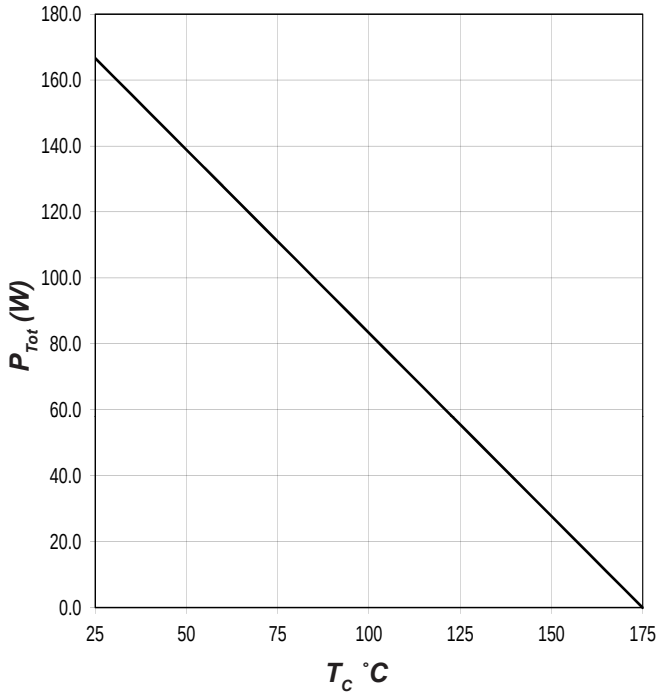


Figure 4. Power Derating

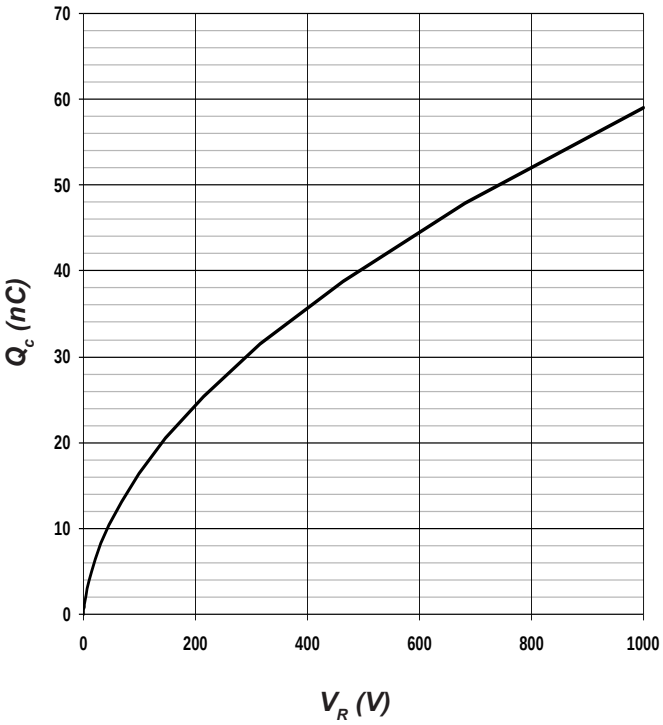


Figure 5. Recovery Charge vs. Reverse Voltage

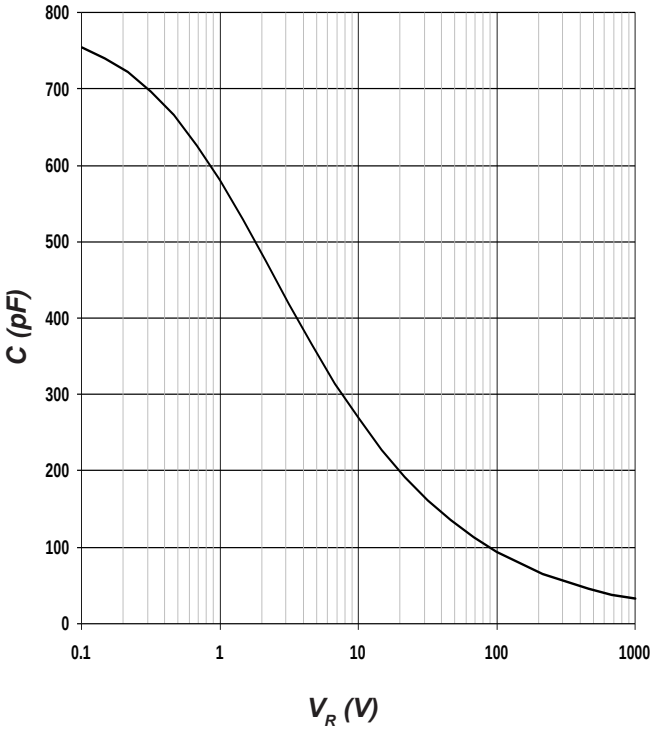


Figure 6. Capacitance vs. Reverse Voltage

Typical Performance

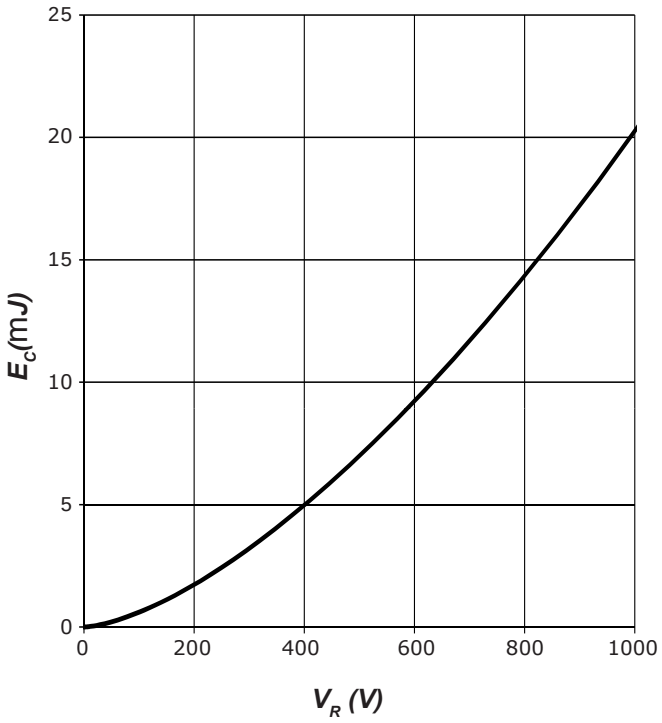


Figure 7. Typical Capacitance Stored Energy

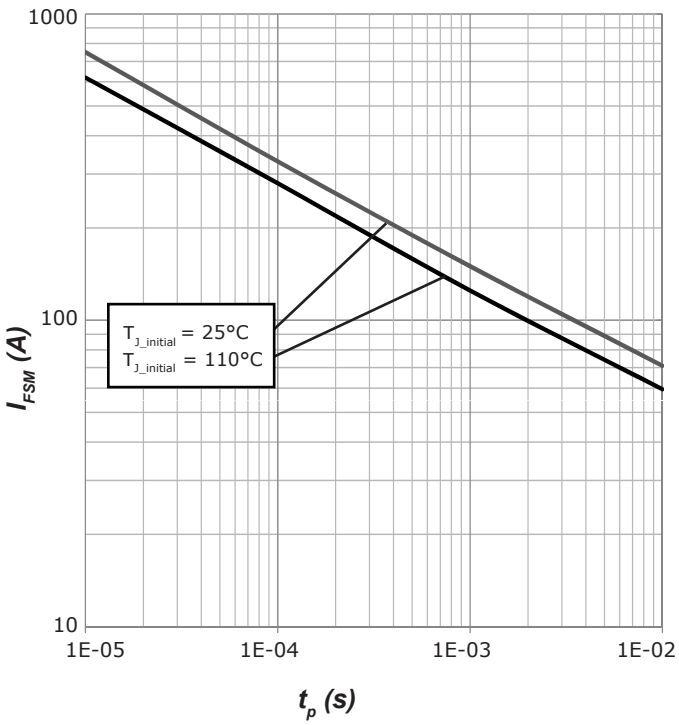


Figure 8. Non-repetitive peak forward surge current versus pulse duration (sinusoidal waveform)

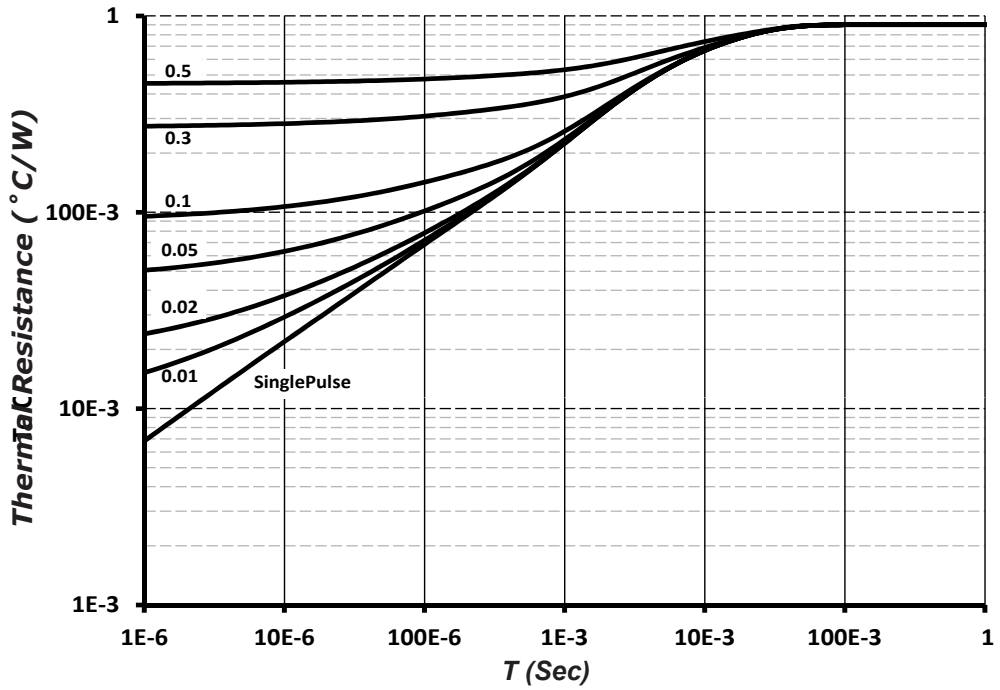
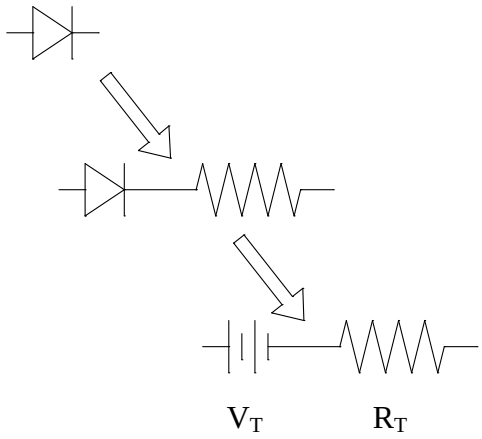


Figure 9. Transient Thermal Impedance

Diode Model

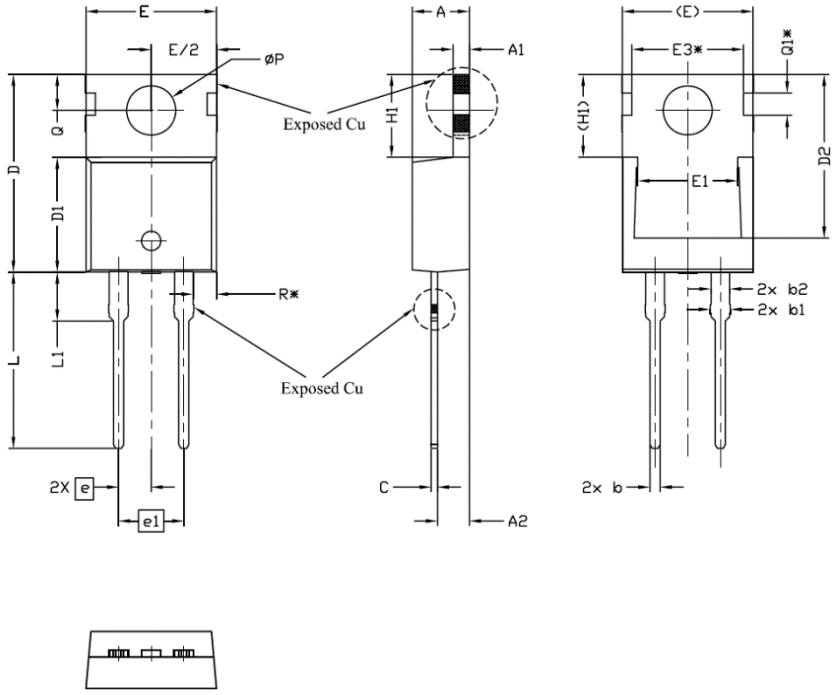


$$V_{fT} = V_T + If * R_T$$

$$V_T = 0.98 + (T_J * -1.71 * 10^{-3})$$
$$R_T = 0.040 + (T_J * 5.32 * 10^{-4})$$

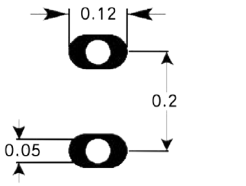
Note: T_J = Diode Junction Temperature In Degrees Celsius, valid from 25°C to 175°C

Package Information
TO-220C-2L



SYMBOL	DIMENSIONS			NOTES
	MIN.	NOM.	MAX.	
A	4.24	4.44	4.64	
A1	1.15	1.27	1.40	
A2	2.30	2.48	2.70	
b	0.70	0.80	0.90	
b1	1.20	1.55	1.75	
b2	1.20	1.45	1.70	
c	0.40	0.50	0.60	
D	14.70	15.37	16.00	4
D1	8.82	8.92	9.02	
D2	12.43	12.73	12.83	5
E	9.96	10.16	10.36	4,5
E1	6.86	7.77	8.89	5
E3*	8.70REF.			
e	2.54BSC			
e1	5.08BSC			
H1	6.30	6.45	6.60	5,6
L	13.47	13.72	13.97	
L1	3.60	3.80	4.00	
ØP	3.75	3.84	3.93	
Q	2.60	2.80	3.00	
Q1*	1.73REF.			
R*	1.82REF.			

Recommended Solder Pad Layout



all units are in inches

TO-220C-2L

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